

EAST - [Untitled1:1]

File View Edit Tools Window Help

L21: (719) 19 and conduct^{s3}
L22: (666) 21 and ((second or upp
L23: (594) 22 and (memory or caps
L24: (296) 23 and silicon
L25: (223) 24 and (size or nanome
L26: (101) 25 and (resist or phot
L27: (32) 26 and (molecular or bi

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26 and (molecular or bistable or rot oxanes or catenanes or pseudorotaxanes)

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U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	F
23	<input type="checkbox"/>	US 5711988 A	19980127	43	Energy storage device and its methods of manufacture	427/80	29/25.01; 29/25.03;	
24	<input type="checkbox"/>	US 5629231 A	19970513	40	Method of manufacturing a semiconductor device with metallic	438/509	257/E29.071; 257/E29.078;	
25	<input checked="" type="checkbox"/>	US 5587264 A	19961224	56	Electrostatic information recording medium and electrostatic	430/57.1	349/3; 430/31;	
26	<input type="checkbox"/>	US 5517342 A	19960514	34	Liquid crystal display having additional capacitors formed from	349/43	349/139; 349/149	
27	<input type="checkbox"/>	US 5502315 A	19960326	13	Electrically programmable interconnect structure having a	257/50	257/530	
28	<input type="checkbox"/>	US 4845533 A	19890704	18	Thin film electrical devices with amorphous carbon electrodes and	257/4		
29	<input type="checkbox"/>	US 4809044 A	19890228	24	Thin film overvoltage protection devices	257/3	257/4; 257/741;	
30	<input type="checkbox"/>	US 4153984 A	19790515	9	Method of fabricating an MNOS memory device	438/287	257/315; 257/632;	
31	<input type="checkbox"/>	US 3795977 A	19740312	9	METHODS FOR FABRICATING BISTABLE RESISTORS	29/25.02	438/104; 438/385	
32	<input type="checkbox"/>	US 3699543 A	19721017	17	COMBINATION FILM DEPOSITED SWITCH UNIT AND INTEGRATED CIRCUITS	365/163	257/57; 257/E27.004;	
								257/500

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